

2N3416_D26Z Datasheet



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DiGi Electronics Part Number 2N3416_D26Z-DG

Manufacturer onsemi

Manufacturer Product Number 2N3416_D26Z

Description TRANS NPN 50V 0.5A TO92-3

Detailed Description Bipolar (BJT) Transistor NPN 50 V 500 mA 625 mW T

hrough Hole TO-92-3



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
2N3416_D26Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
50 V	300mV @ 3mA, 50mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	75 @ 2mA, 4.5V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	
2N341	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095



2N3416 2N3417



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		2N3416 / 2N3417		
P_D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

NPN General Purpose Amplifier

Min

(continued)

Units

Max

Electrical	Characteristics	TA = 2

Parameter

TA = 25°C unless otherwise noted

Test Conditions

OFF CHA	ARACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	I _C = 10 mA, I _B = 0	50		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	50		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 18 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$		100 15	nA μA
I _{EBO}	Emitter-Cutoff Current	V _{EB} = 5.0 V, I _C = 0		100	nA

ON CHARACTERISTICS*

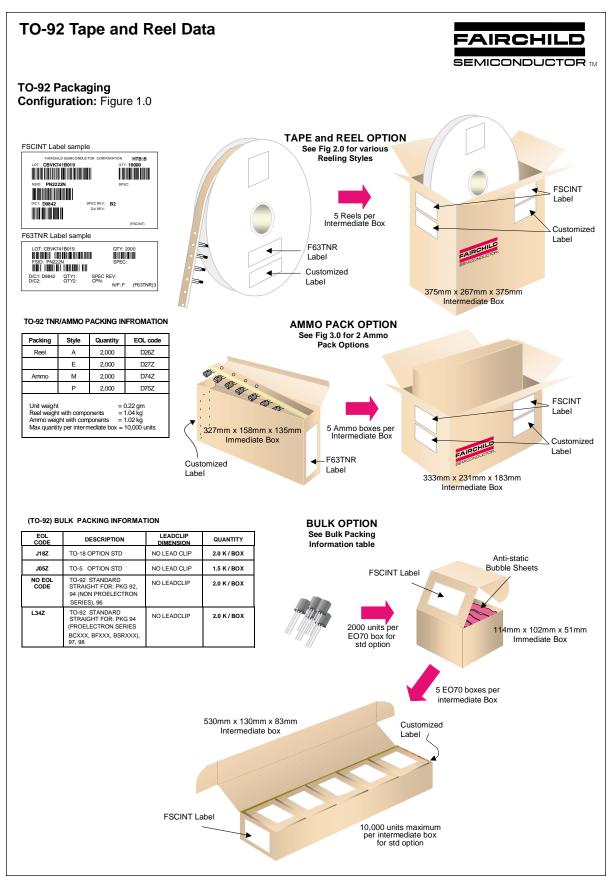
Symbol

h _{FE}	DC Current Gain	$V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$			
		2N3416	75	225	
		2N3417	180	540	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$		0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$	0.6	1.3	V

SMALL SIGNAL CHARACTERISTICS

h _{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} =$			
		f = 1.0 kHz	2N3416	75	
			2N3417	180	

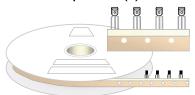
^{*}Pulse Test: Pulse Width $\leq\!300~\mu\text{s}$, Duty Cycle $\leq\!2.0\%$



TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

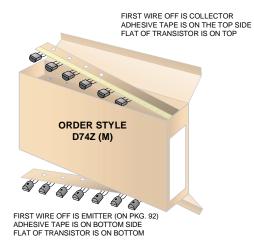


Style "A", D26Z, D70Z (s/h)

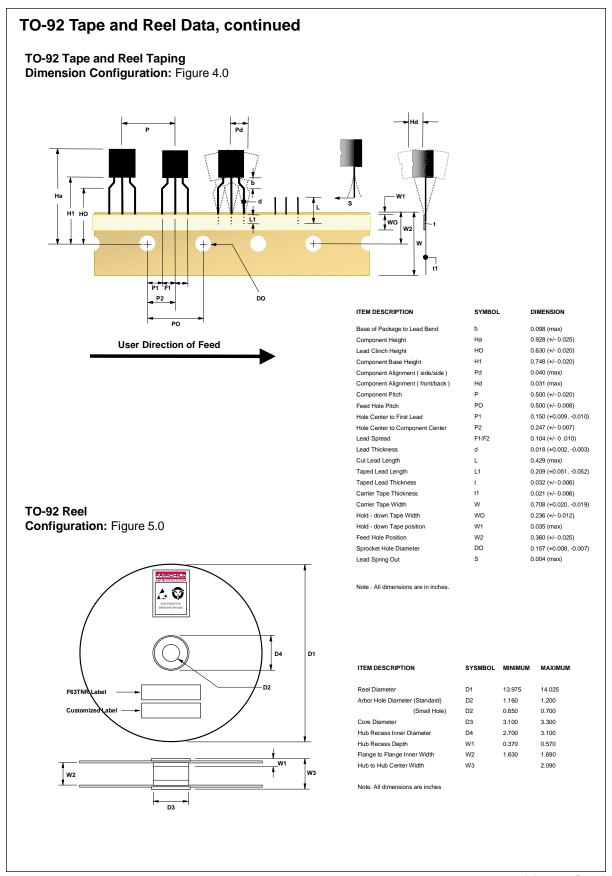
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0







TO-92 Package Dimensions SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 В В B F В D 2 В S С G Ε D Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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FACT Quiet Series PACMAN SuperSOT**-6
FAST POPT**
SuperSOT**-8

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